



STB120NF10 STP120NF10

N-CHANNEL 100V - 0.009 Ω - 120A D²PAK/TO-220
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB120NF10	100 V	< 0.0105 Ω	120 A
STP120NF10	100 V	< 0.0105 Ω	120 A

- TYPICAL R_{DS(on)} = 0.009 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- SURFACE-MOUNTING D²PAK (TO-263)
POWER PACKAGE IN TAPE & REEL
(SUFFIX "T4")

DESCRIPTION

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize the on-resistance. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

APPLICATIONS

- AUDIO AMPLIFIERS
- POWER TOOLS

Ordering Information

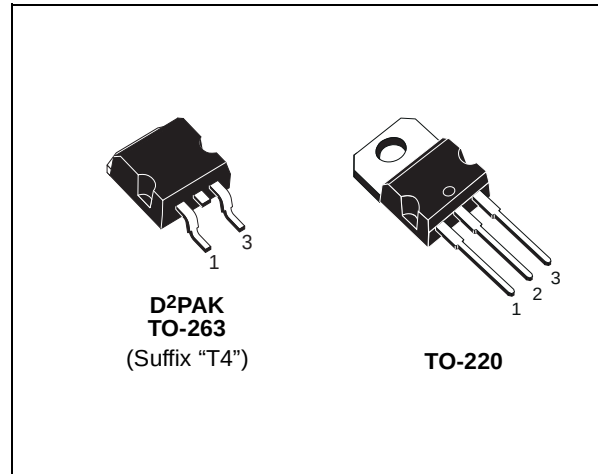
SALES TYPE	MARKING	PACKAGE	PACKAGING
STB120NF10	B120NF10	TO-263	TAPE & REEL
STP120NF10	P120NF10	TO-220	TUBE

ABSOLUTE MAXIMUM RATINGS

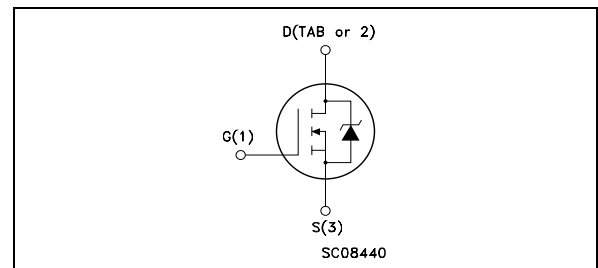
Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	100	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	120	A
I _D	Drain Current (continuous) at T _C = 100°C	85	A
I _{DM} (●)	Drain Current (pulsed)	480	A
P _{tot}	Total Dissipation at T _C = 25°C	312	W
	Derating Factor	2.08	W/°C
dv/dt ⁽¹⁾	Peak Diode Recovery voltage slope	10	V/ns
E _{AS} ⁽²⁾	Single Pulse Avalanche Energy	550	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(●) Pulse width limited by safe operating area.

(1) I_{SD} ≤ 120A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}
(2) Starting T_j = 25 °C, I_D = 60A, V_{DD} = 50V



INTERNAL SCHEMATIC DIAGRAM



STB120NF10 STP120NF10**THERMAL DATA**

R _{thj-case}	Thermal Resistance Junction-case	Max	0.48	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 60 A		0.009	0.0105	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 60 A		TBD		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		5200 785 325		pF pF pF

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ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		25 90		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=80\text{ V}$ $I_D=120\text{ A}$ $V_{GS}=10\text{ V}$		172 32 64	233	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		132 68		ns ns

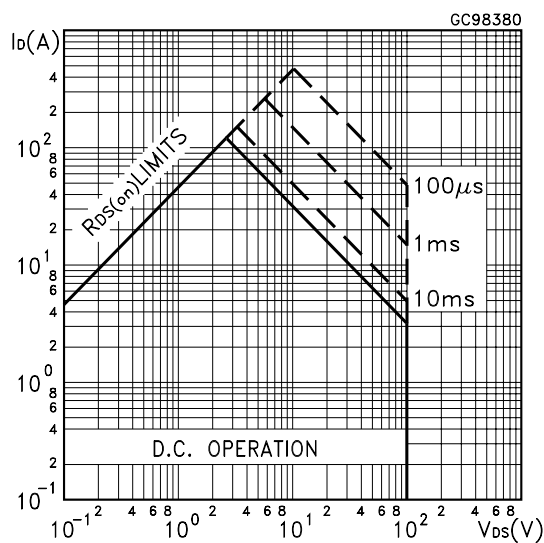
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				120 480	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 120\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 120\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 40\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		152 760 10		ns nC A

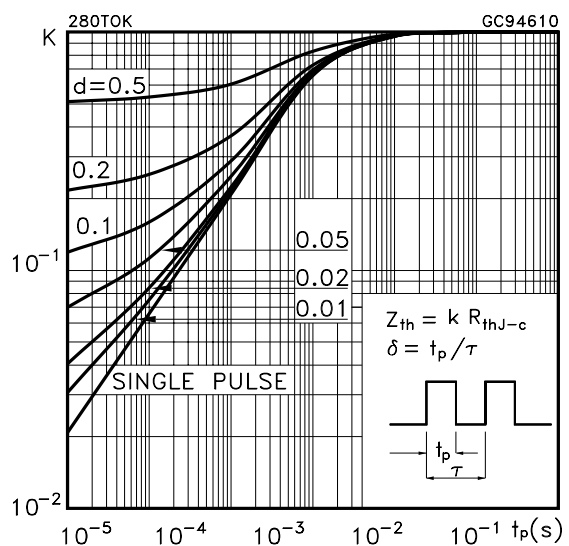
(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

($\bullet$)Pulse width limited by safe operating area.

Safe Operating Area

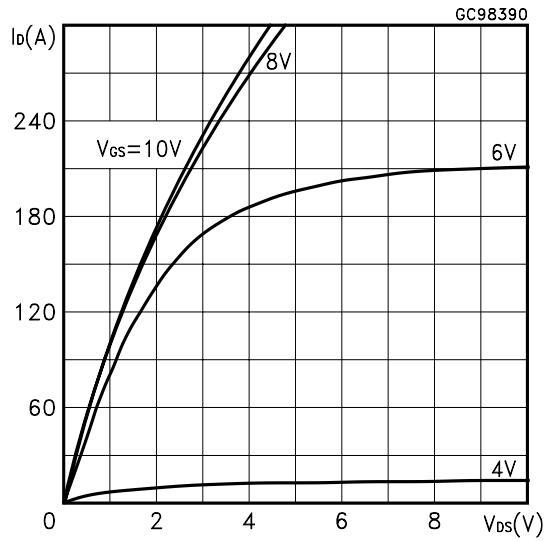


Thermal Impedance

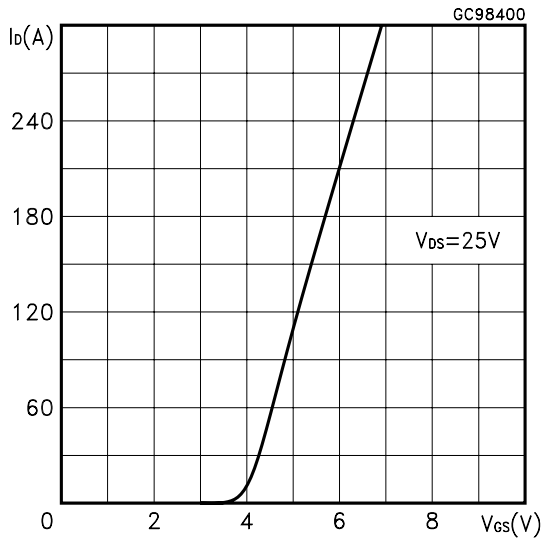


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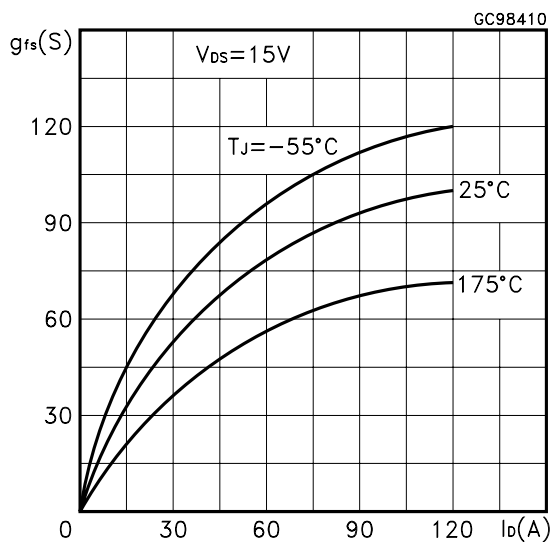
Output Characteristics



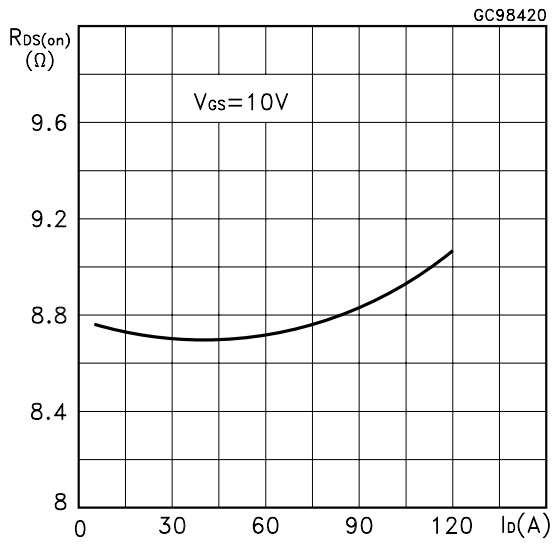
Transfer Characteristics



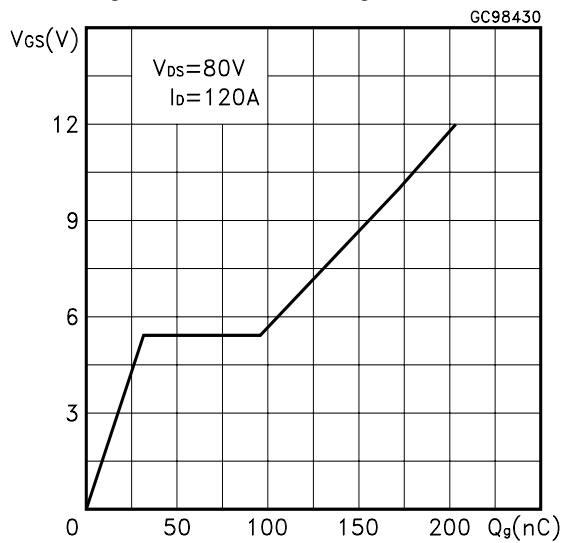
Transconductance



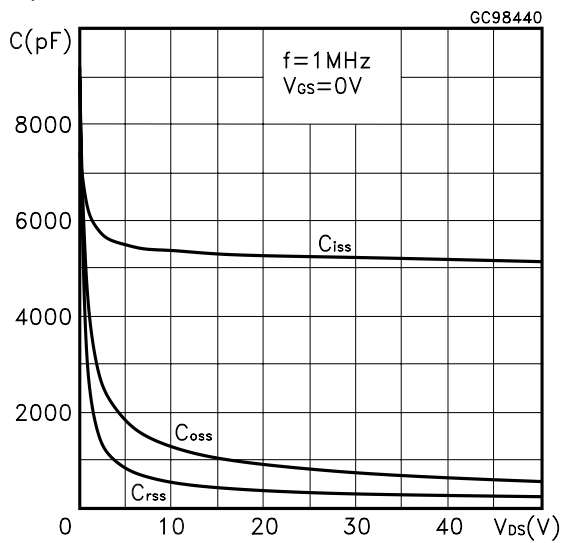
Static Drain-source On Resistance



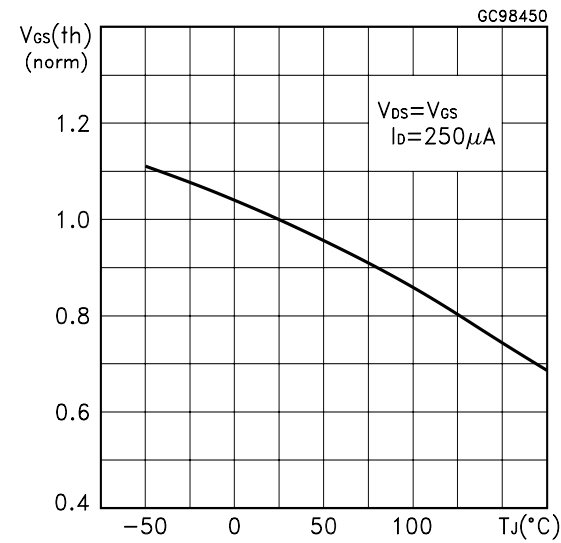
Gate Charge vs Gate-source Voltage



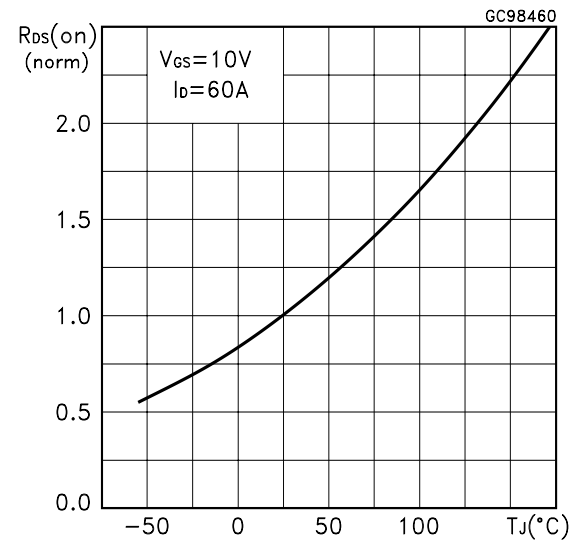
Capacitance Variations



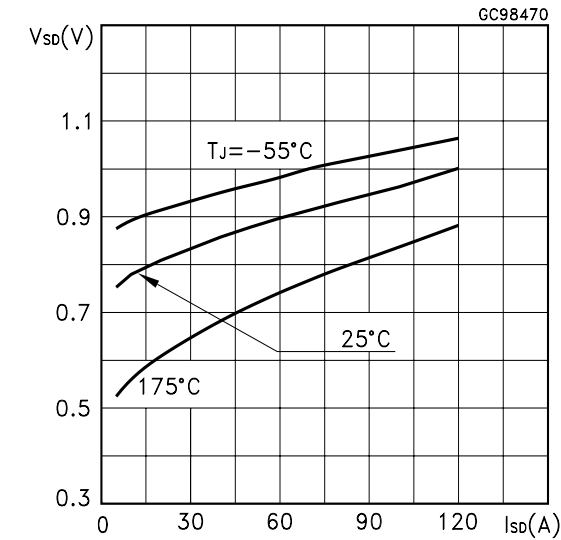
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature

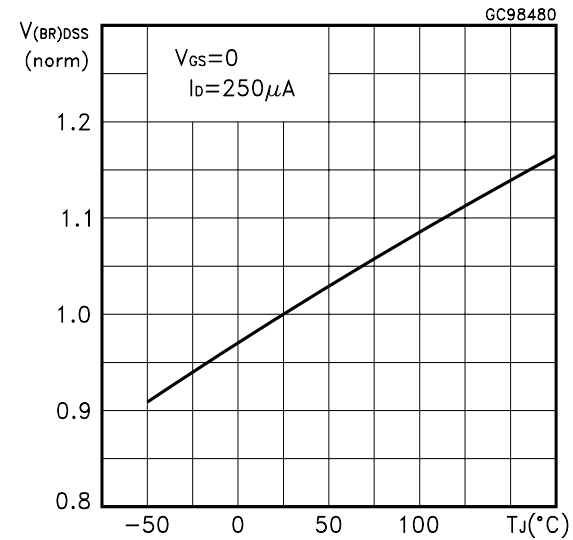


Fig. 1: Unclamped Inductive Load Test Circuit

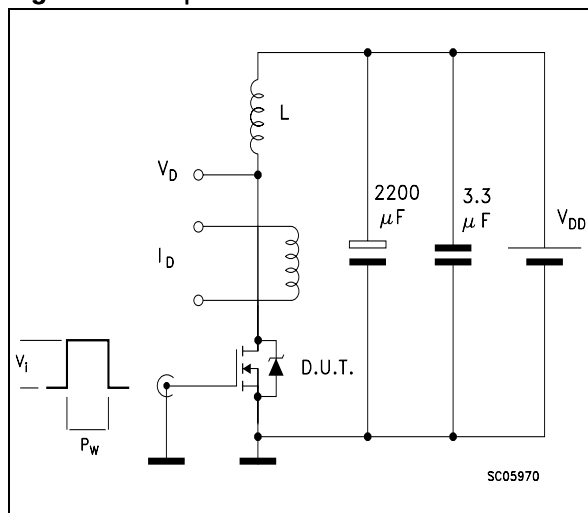


Fig. 2: Unclamped Inductive Waveform

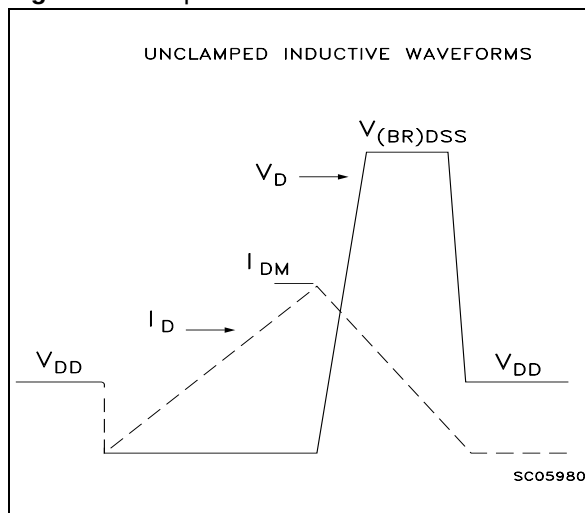


Fig. 3: Switching Times Test Circuits For Resistive Load

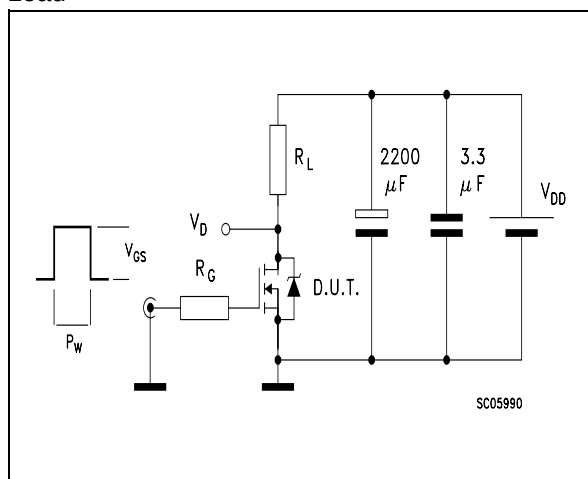


Fig. 4: Gate Charge test Circuit

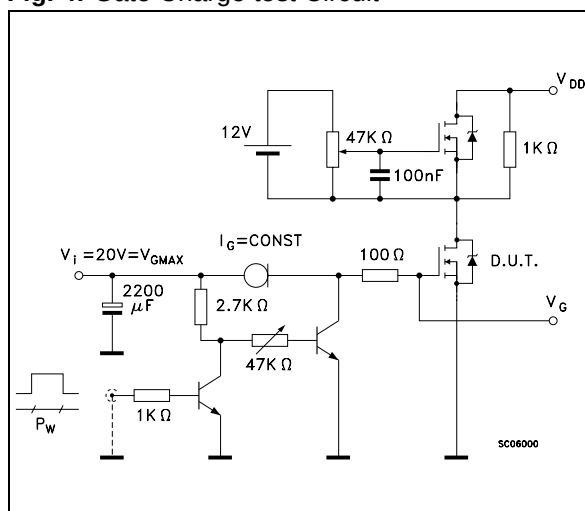
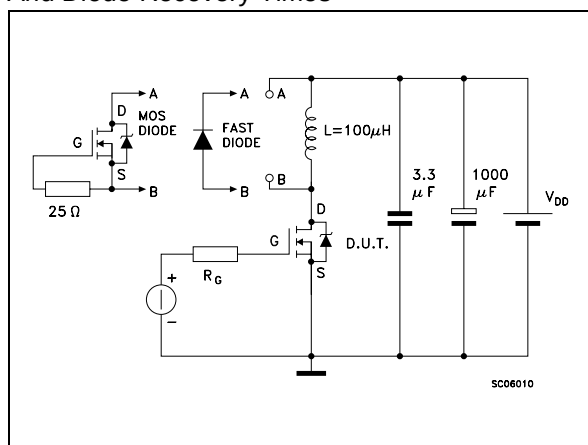
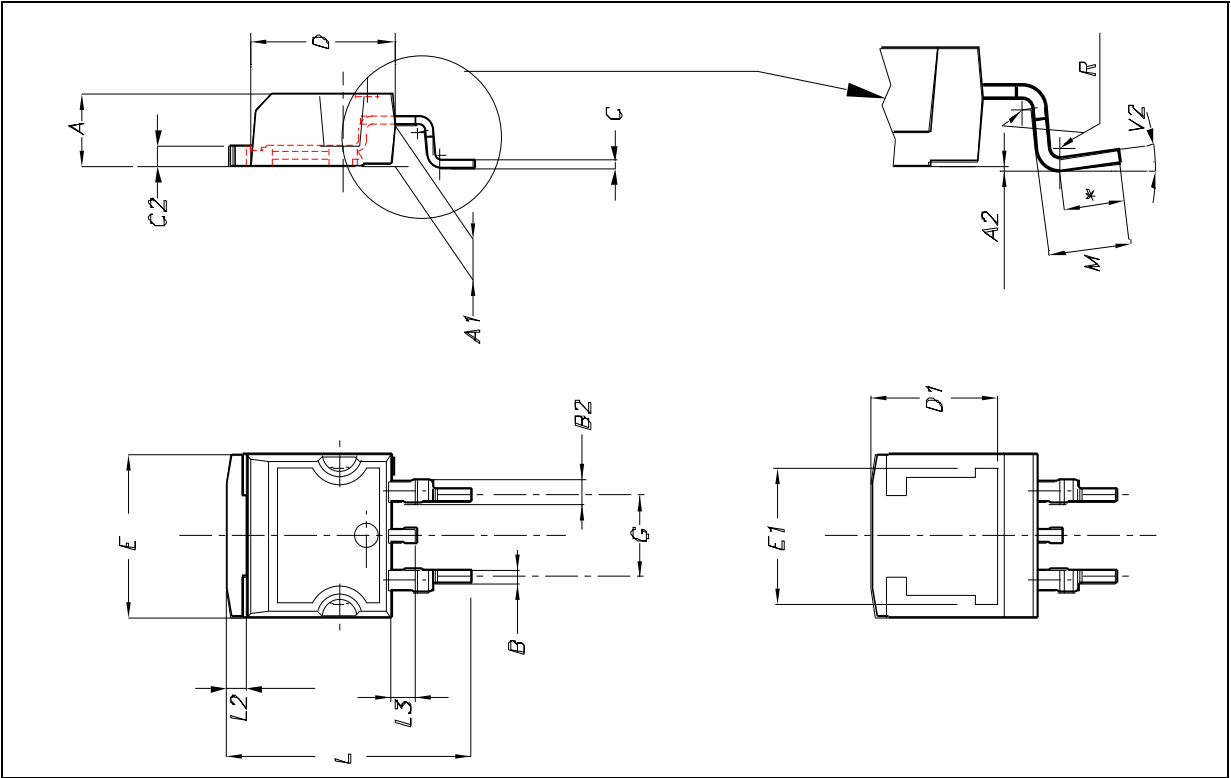


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



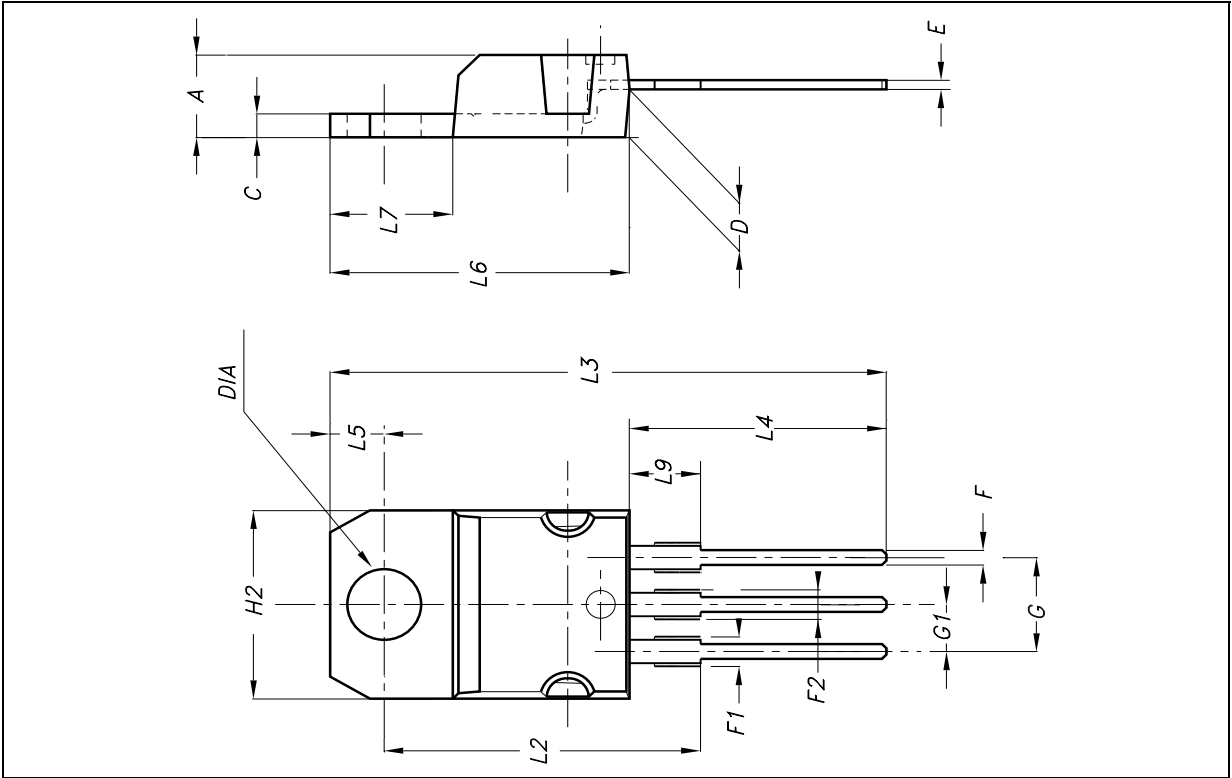
D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°	0°		8°

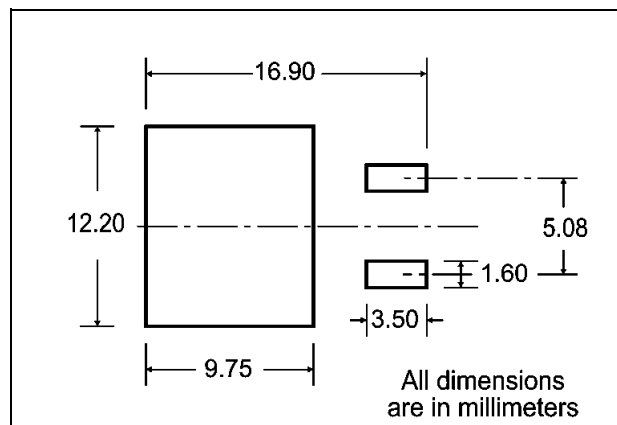


TO-220 MECHANICAL DATA

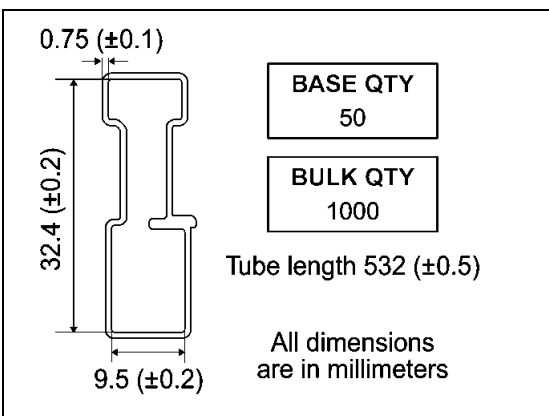
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



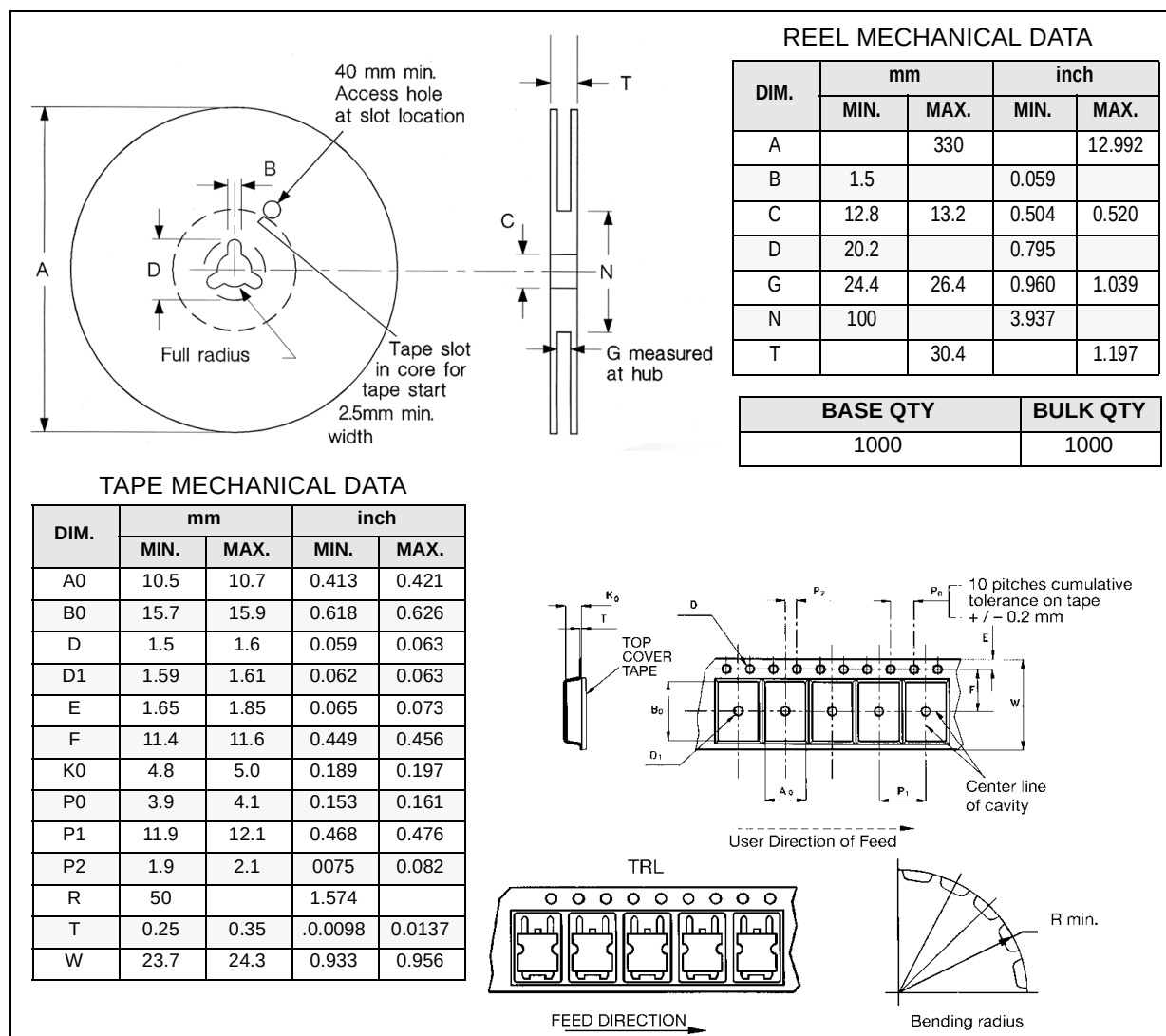
D2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales type

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